

**Amendments to the Specification:**

On page 2, please replace paragraph [0008] with the following new paragraph:

Referring now to **Fig. 2**, in an embodiment a gap fill test pattern such as for a shallow trench isolation (STI) gap fill comprises one or more test regions 10,20. Each test region 10,20 further comprises an outer circumference (e.g. comprising sides 11 and 12 or sides 21 and 22) defining first interior area 19, 29 and test pattern 18, ~~28~~ 26 disposed in first interior area 19, 29.

On page 2, please replace paragraph [0011] with the following new paragraph:

In other embodiments, a non-square rectangular region 20 may comprise an area of around from around  $1 \mu\text{m}^2$  to around  $3 \mu\text{m}^2$  and test pattern ~~28~~ 26 may define a rectangle, comprising border 27 comprising width 23 ranging from around  $0.085 \mu\text{m}$  to around  $0.200 \mu\text{m}$ . Test pattern rectangle ~~28~~ 26 further comprises height 25 which be around one-half height 21 of non-square rectangular region 20.

On page 3, please replace paragraph [0013] with the following new paragraph:

Test regions 10, 20 which comprise a ~~contiguous~~ continuous border 17, 27 (**Fig. 2**) may be adapted to simulate a corner region of a static random access memory cell (not shown in the figures). Test regions 10, 20 which comprise at least one discontinuity 34, 44 (**Fig. 3**) may be adapted to simulate an outer diameter line end region of a static random access memory cell (not shown in the figures). Discontinuity 34, 44 may be configured as a gap of around  $0.1 \mu\text{m}$ .

On page 3, please replace paragraph [0014] with the following new paragraph:

In certain embodiments, a plurality of discontinuities 34, 44 (**Fig. 3**) may be present in test pattern 18, ~~28~~ 26, defining a plurality of discontinuous border segments 37, 38 and 47, 48.

Each border segment 37, 38 and 47, 48 may further comprise a first section intersecting a second section. In a preferred embodiment the first section intersects the second section at a substantially right angle.

On page 3, please replace paragraph [0015] with the following new paragraph:

Each test pattern 18, ~~28~~ 26 may be fabricated using a shallow trench adapted for testing of shallow trench isolation gap fill, the test pattern (18, ~~28~~ 26) defining a border (17, 27) to that encloses a second interior area (16, ~~26~~ 28).

On page 3, please replace paragraph [0016] with the following new paragraph:

Referring to either Fig. 2 or Fig. 3, a gap fill test region pattern for an STI gap fill may comprise test area 100 fabricated on a predetermined region of a semiconductor wafer. Test area 100 may further comprise border 101 and ~~first interior~~ test region area 102. A plurality of the test regions 10, 20 may be disposed within ~~first interior~~ the test region area 102, each of the test regions 10, 20 comprising ~~second~~ the first interior area 19, 29 and the border 17, 27 ~~where border~~ ~~17, 27 defines third and the second~~ interior area 16, ~~236~~ 28, the test pattern further comprising at least one shallow trench adapted for testing of shallow trench isolation gap fill.